STTA312B

TURBOSWITCH™ ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	**3 A**
V_{RRM}	**1200 V**
t_{rr} **(typ)**	**65 ns**
V_F **(max)**	**1.7 V**

FEATURES AND BENEFITS

- SPECIFIC TO THE FOLLOWING OPERATIONS: SNUBBING OR CLAMPING, DEMAGNETIZATION AND RECTIFICATION
- ULTRA-FAST, SOFT RECOVERY
- VERY LOW OVERALL POWER LOSSES AND PARTICULARY LOW FORWARD VOLTAGE
- HIGH FREQUENCY OPERATION
- HIGH REVERSE VOLTAGE CAPABILITY

DPAK

DESCRIPTION

TURBOSWITCH 1200V drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes.

Due to their optimized switching performances they also highly decrease power losses in any associated switching IGBT or MOSFET in all "freewheel mode" operations.

They are particularly suitable in motor control circuitries, or in primary of SMPS as snubber, clamping or demagnetizing diodes. They are also suitable for the secondary of SMPS as high voltage rectifier diodes.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		1200	V
V_{RSM}	Non repetitive peak reverse voltage		1200	V
$I_{F(RMS)}$	RMS forward current		6	A
I_{FRM}	Repetitive peak forward current	tp = 5 µs F = 5kHz square	35	A
I_{FSM}	Surge non repetitive forward current	tp = 10ms sinusoidal	25	A
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum operating junction temperature		125	°C

THERMAL AND POWER DATA

Symbol	Parameter	Tests conditions	Value	Unit
$R_{th\ (j-c)}$	Junction to case thermal resistance		6.5	°C/W
P_1	Conduction power dissipation	$I_{F(AV)} = 3A, \delta = 0.5$ Tc = 80°C	6.7	W
P_{max}	Total power dissipation $P_{max} = P_1 + P_3$ ($P_3 = 10\% P_1$)	Tc = 76°C	7.5	W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
V_F **	Forward voltage drop	$I_F = 3\ A$	Tj = 25°C			1.8	V
		$I_F = 3\ A$	Tj = 125°C		1.15	1.7	
I_R *	Reverse leakage current	$V_R = 0.8$ X V_{RRM}	Tj = 25°C			20	µA
			Tj = 125°C		150	400	µA
Vto	Threshold voltage	$Ip < 3.I_{AV}$	Tj = 125°C			1.15	V
rd	Dynamic resistance					185	mΩ

Test pulses :   * tp = 380 µs, δ < 2%
                   ** tp = 5 ms , δ < 2%

To evaluate the maximum conduction losses use the following equation :
$P = V_{to} \times I_{F(AV)} + rd \times I_F^2{}_{(RMS)}$
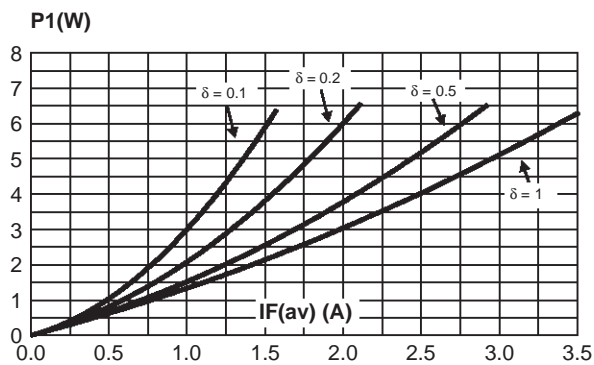
DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
t_{rr}		Tj = 25°C	I_F= 0.5A I_R=1A I_{rr}= 0.25A I_F= 1A dI_F/dt= 50A/µs V_R= 30V		65	115	ns
I_{RM}	Maximum recovery current	Tj = 125°C	I_F= 3A V_R= 600V dI_F/dt = -16A/µs dI_F/dt = -50A/µs		6.0	3.6	A
S factor	Softness factor	Tj = 125°C	V_R= 600V I_F= 3A dI_F/dt = -50A/µs		1.2		-

TURN-ON SWITCHING

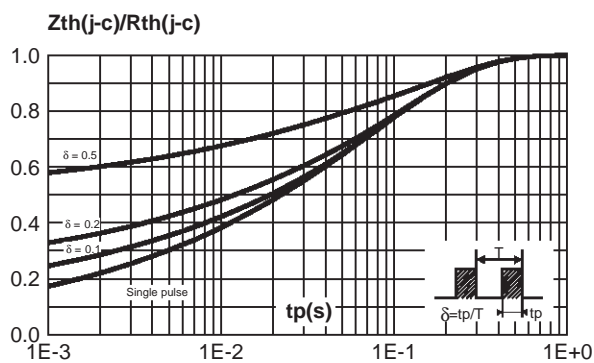| Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{fr}	Forward recovery time	Tj = 25°C I_F=3A dI_F/dt = 16A/µs Measured at 1.1 x V_{Fmax}			900	ns
V_{FP}	Peak forward voltage				35	V

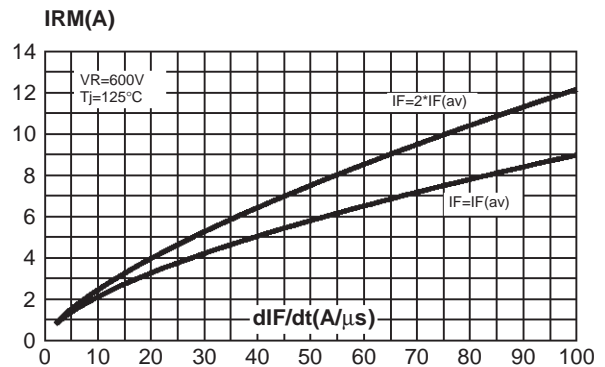**Fig. 1:** Conduction losses versus average current.

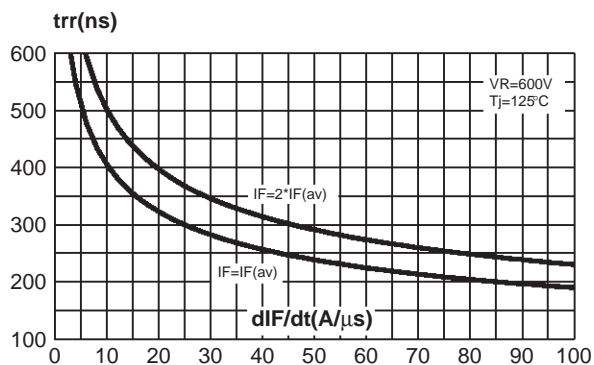**Fig. 2:** Forward voltage drop versus forward current (maximum values).

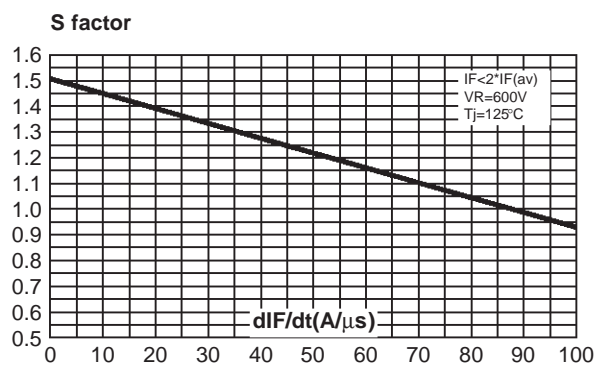**Fig. 3:** Relative variation of thermal impedance junction to case versus pulse duration.

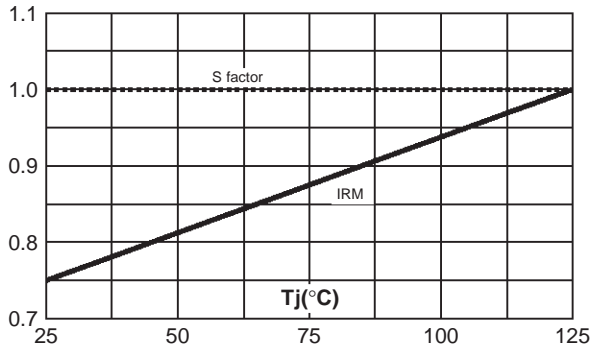**Fig. 4:** Peak reverse recovery current versus dIF/dt (90% confidence).

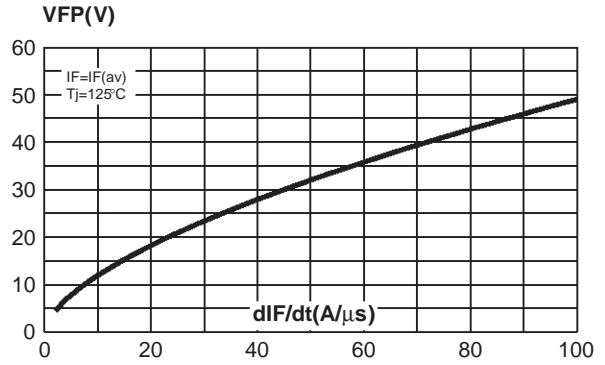**Fig. 5:** Reverse recovery time versus dIF/dt (90% confidence).

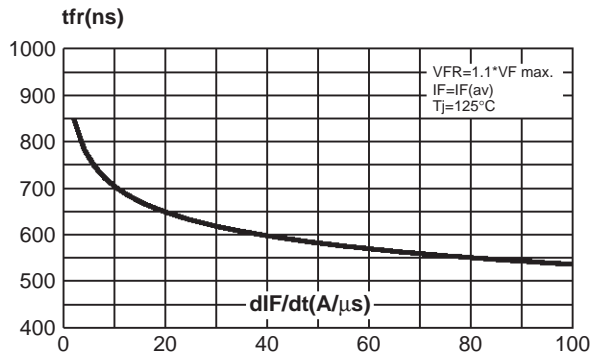**Fig. 6:** Softness factor tb/ta versus dIF/dt (typical values).

Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: Tj=125°C).

Fig. 8: Transient peak forward voltage versus dI$_F$/dt (90% confidence).

Fig. 9: Forward recovery time versus dI$_F$/dt (90% confidence).

APPLICATION DATA

The 1200V TURBOSWITCH^{TM} series has been designed to provide the lowest overall power losses in all frequency or high pulsed current operations.

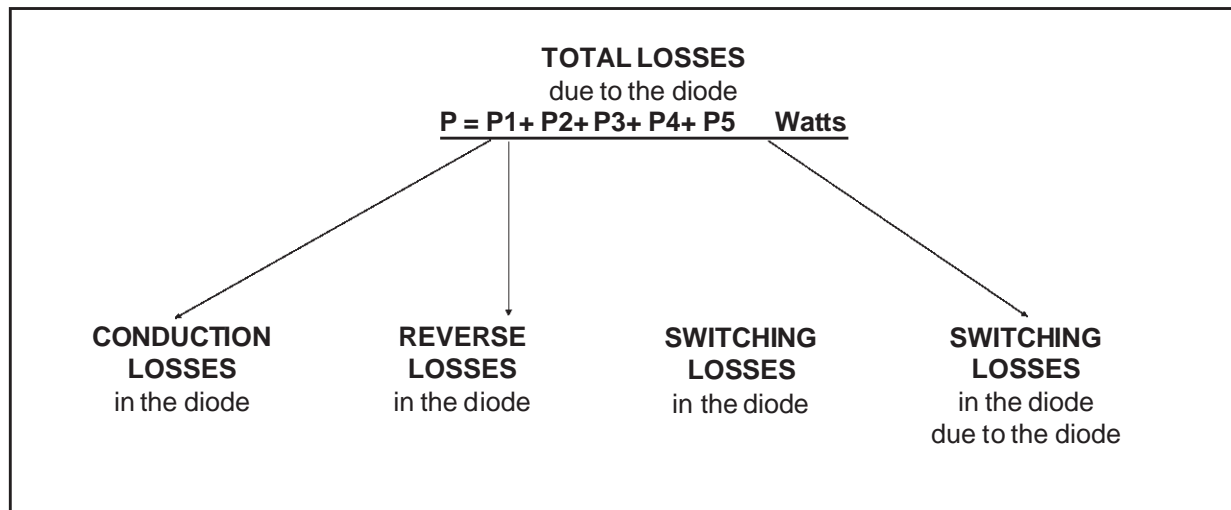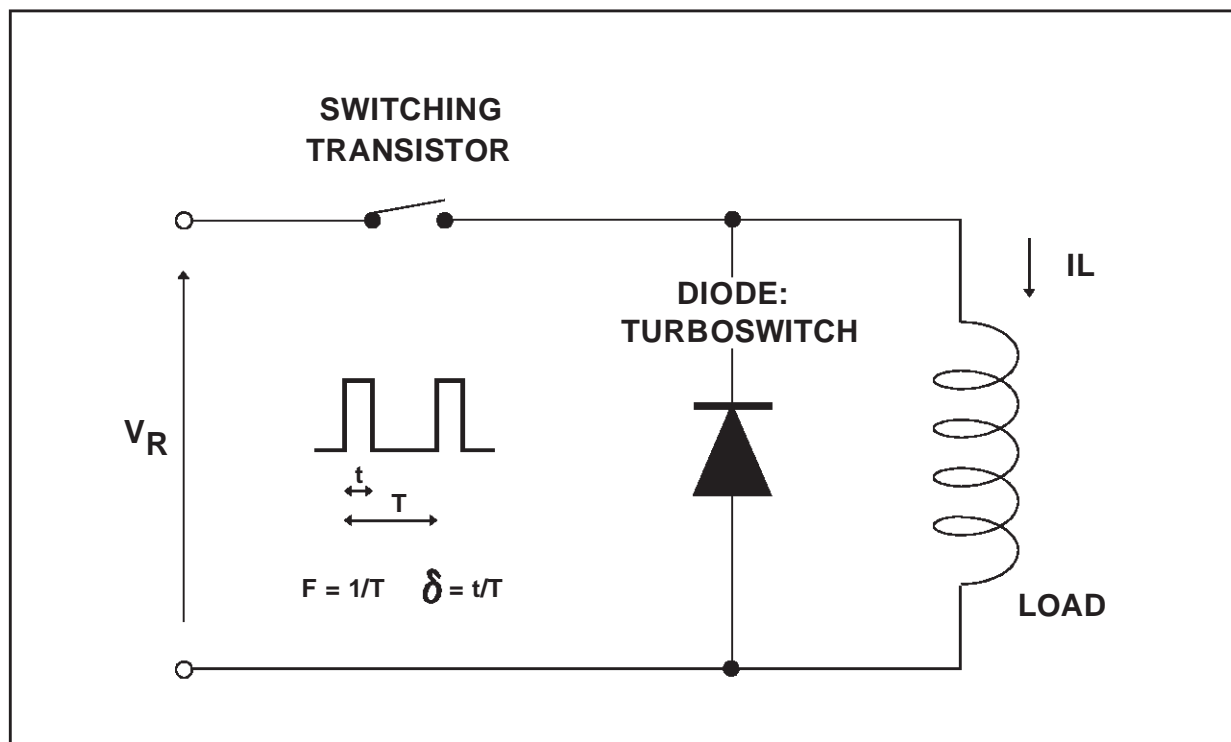In such application (fig. A to D), the way of calculating the power losses is given below :

TOTAL LOSSES
due to the diode
P = P1+ P2+ P3+ P4+ P5   Watts

CONDUCTION LOSSES	**REVERSE LOSSES**	**SWITCHING LOSSES**	**SWITCHING LOSSES**
in the diode	in the diode	in the diode	in the diode due to the diode

Fig. A : "FREEWHEEL MODE"**.**

SWITCHING TRANSISTOR

DIODE: TURBOSWITCH

IL

V_R

$F = 1/T$ δ = t/T

LOAD

APPLICATION DATA (Cont'd)
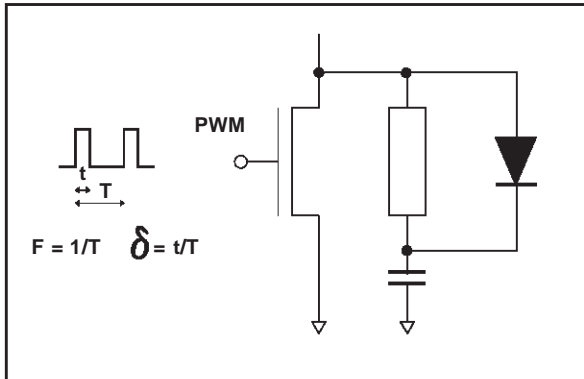
Fig. B : SNUBBER DIODE.
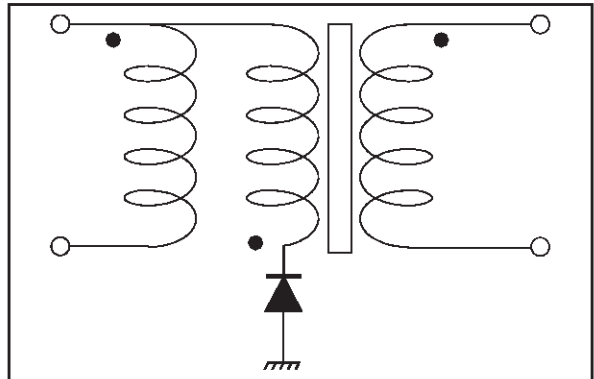

Fig. C : DEMAGNETIZING DIODE.
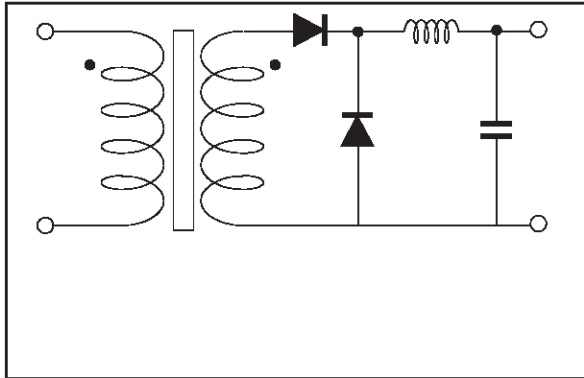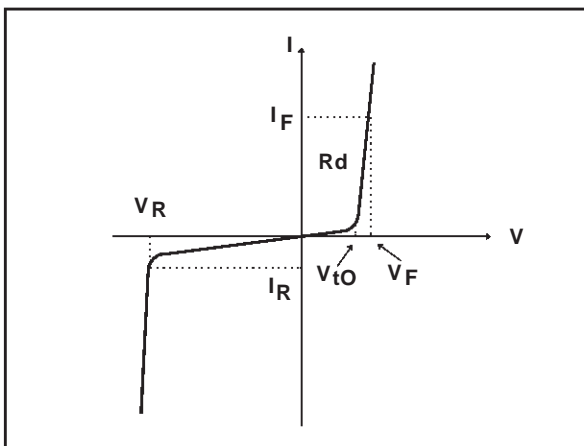

Fig. D : RECTIFIER DIODE.

Fig. E : STATIC CHARACTERISTICS.

Conduction losses :

$$P1 = V_{t0} \times I_{F(AV)} + R_d \times I_F^2{}_{(RMS)}$$

Reverse losses :

$$P2 = V_R \times I_{R \times (1-\delta)}$$

APPLICATION DATA (Cont'd)
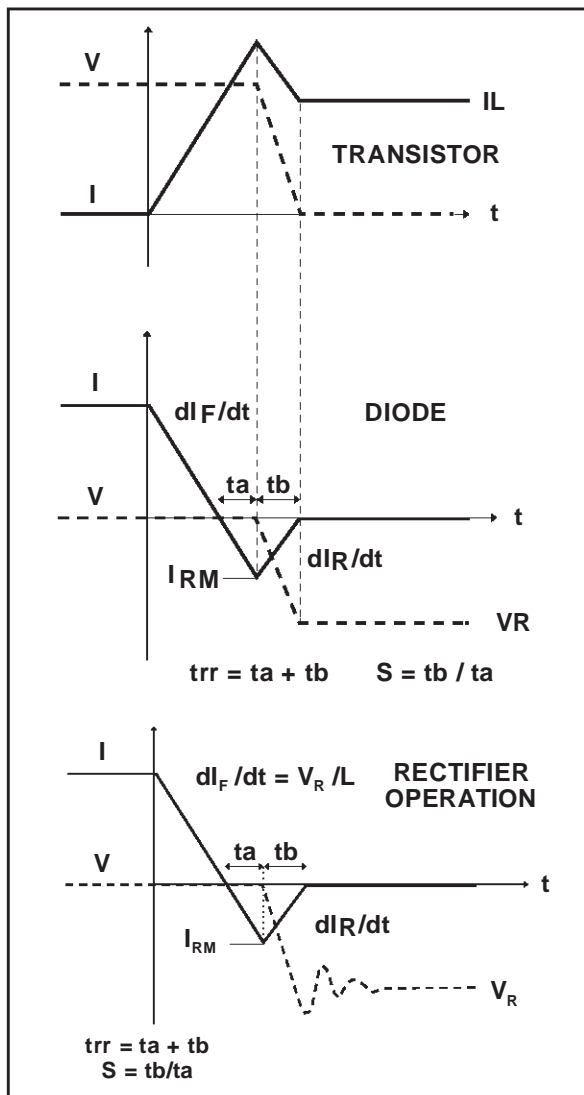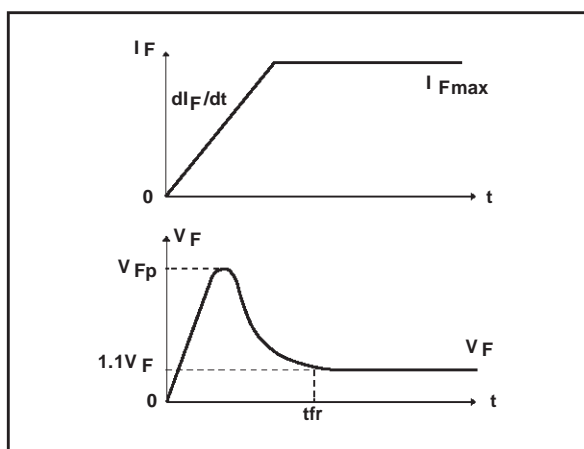
Fig. F : TURN-OFF CHARACTERISTICS.

Fig. G : TURN-ON CHARACTERISTICS.

Turn-on losses :
(in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}{}^2 \times (3+2 \times S)\ F}{6 \times dI_F/dt}$$
$$+ \frac{V_R \times I_{RM} \times I_L \times (S+2) \times F}{2 \times dI_F/dt}$$

Turn-off losses :

$$P3 = \frac{V_R \times I_{RM}{}^2 \times \times S \times F}{6 \times dI_F/dt}$$

Turn-off losses :
with non negligible serial inductance

$$P3' = \frac{V_R \times I_{RM}{}^2 \times S \times F}{6 \times dI_F/dt} + \frac{L \times I_{RM}{}^2 \times F}{2}$$

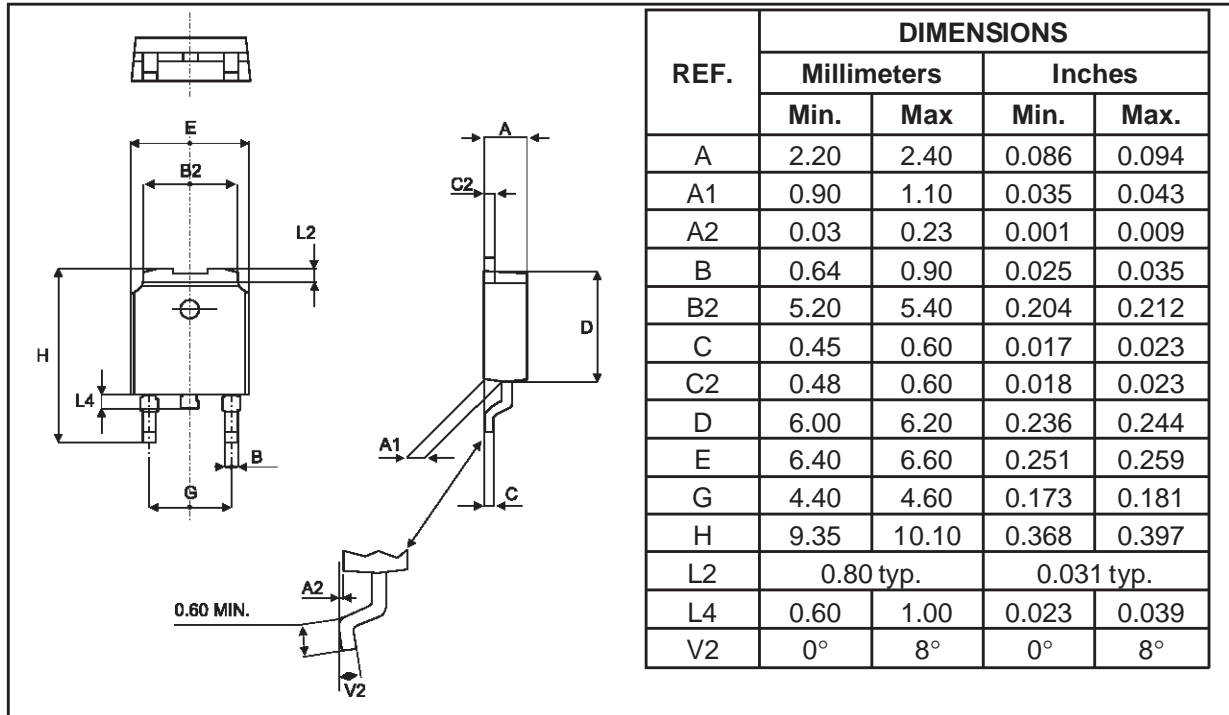P3, P3' and P5 are suitable for power MOSFET and IGBT

Turn-on losses :
P4 = 0.4 (V_{FP} - V_F) x I_{Fmax} x t_{fr} x F

STTA312B

PACKAGE MECHANICAL DATA
DPAK

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max	Min.	Max.
A	2.20	2.40	0.086	0.094
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
B	0.64	0.90	0.025	0.035
B2	5.20	5.40	0.204	0.212
C	0.45	0.60	0.017	0.023
C2	0.48	0.60	0.018	0.023
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.251	0.259
G	4.40	4.60	0.173	0.181
H	9.35	10.10	0.368	0.397
L2	0.80 typ.		0.031 typ.	
L4	0.60	1.00	0.023	0.039
V2	0°	8°	0°	8°

FOOTPRINT DIMENSIONS (in millimeters)

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTA312B	A312	DPAK	0.3g	75	Tube
STTA312B-TR	A312	DPAK	0.3g	2500	Tape & reel

■ Epoxy meets UL94, V0